



NPN SILICON TRANSISTOR

2SC2408

DESCRIPTION 2SC2408 is designed for High frequency Wide Band Amplifier.

- FEATURES**
- $|S_{21e}|^2$: 21 dB TYP. @200 MHz
 - NF : 2.4 dB TYP. @200 MHz

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage Temperature -65 to +150 °C

Junction Temperature +150 °C Maximum

Maximum Power Dissipation (Ta=25 °C)

Total Power Dissipation 600 mW

Maximum Voltages and Current (Ta=25 °C)

V_{CBO} Collector to Base Voltage 35 V

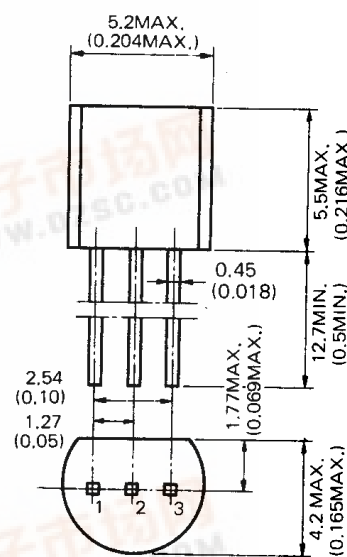
V_{CEO} Collector to Emitter Voltage 18 V

V_{EBO} Emitter to Base Voltage 3.0 V

I_C Collector Current 150 mA

PACKAGE DIMENSIONS

in millimeters (inches)



- 1. BASE EIAJ : SC-43A
- 2. EMITTER JEDEC : TO-92
- 3. COLLECTOR IEC : PA33

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h _{FE}	DC Current Gain	30	100	200		V _{CE} =10 V, I _C =50 mA
f _T	Gain Bandwidth Product		3.5		GHz	V _{CE} =10 V, I _E =50 mA
C _{ob}	Output Capacitance		1.25	2.0	pF	V _{CB} =10 V, I _E =0, f=200 MHz
S _{21e} ²	Insertion Power Gain	18	21		dB	V _{CE} =10 V, I _C =50 mA, f=200 MHz, R _G =50 Ω
NF	Noise Figure		2.4	4.0	dB	V _{CE} =10 V, I _C =30 mA, f=200 MHz, R _G =50 Ω
I _{CBO}	Collector Cutoff Current			0.5	μA	V _{CB} =20 V, I _E =0
I _{EBO}	Emitter Cutoff Current			0.5	μA	V _{EB} =2.0 V, I _C =0

